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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/614,286	07/12/2000	Hiroshi Tanabe	NECK 17.552	2375
26304	7590 11/08/2002			
KATTEN MUCHIN ZAVIS ROSENMAN			EXAMINER	
575 MADISO NEW YORK,	NY 10022-2585		KIELIN, ERIK J	
			ART UNIT	PAPER NUMBER
			2813	20
			DATE MAILED: 11/08/2002	0

Please find below and/or attached an Office communication concerning this application or proceeding.

		Mr.			
	Application N .	Applicant(s)			
Offic Action Summary	09/614,286	TANABE, HIROSHI			
ome Action Summary	Examiner	Art Unit			
The AAAH INO DATE of this assumption is	Erik Kielin	2813			
Th MAILING DATE of this communication a Peri d for Reply	ppears on the cover sneet w	ith the correspondence address			
A SHORTENED STATUTORY PERIOD FOR REF THE MAILING DATE OF THIS COMMUNICATION - Extensions of time may be available under the provisions of 37 CFR after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a re - If NO period for reply is specified above, the maximum statutory perions - Failure to reply within the set or extended period for reply will, by state - Any reply received by the Office later than three months after the mained patent term adjustment. See 37 CFR 1.704(b). Status	I. 1.136(a). In no event, however, may a eply within the statutory minimum of thin od will apply and will expire SIX (6) MON ute, cause the application to become A	reply be timely filed ty (30) days will be considered timely. ITHS from the mailing date of this communication. 3ANDONED (35 U.S.C. § 133).			
1) Responsive to communication(s) filed on 7/	/25/02, 8/29/02, and 10/4/02				
2a) ☐ This action is FINAL . 2b) ☑ -	This action is non-final.				
3) Since this application is in condition for allocallocallocallocallocallocallocallo	wance except for formal ma er <i>Ex parte Quayle</i> , 1935 C.	tters, prosecution as to the merits is D. 11, 453 O.G. 213.			
4) Claim(s) 1-10 is/are pending in the applicati	on.				
4a) Of the above claim(s) is/are withdrawn from consideration.					
5) Claim(s) is/are allowed.					
6)⊠ Claim(s) <u>1-10</u> is/are rejected.					
7) Claim(s) is/are objected to.					
8) Claim(s) are subject to restriction and	/or election requirement.				
Application Papers					
9)☐ The specification is objected to by the Examir	ner.				
10) ☐ The drawing(s) filed on is/are: a) ☐ acc	cepted or b) objected to by t	he Examiner.			
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).					
11) ☐ The proposed drawing correction filed on is: a) ☐ approved b) ☐ disapproved by the Examiner.					
If approved, corrected drawings are required in reply to this Office action.					
12) ☐ The oath or declaration is objected to by the Examiner.					
Pri rity under 35 U.S.C. §§ 119 and 120					
13) Acknowledgment is made of a claim for foreign	gn priority under 35 U.S.C.	§ 119(a)-(d) or (f).			
a) ☐ All b) ☐ Some * c) ☐ None of:					
 Certified copies of the priority document 	nts have been received.				
Certified copies of the priority document	nts have been received in A	pplication No			
3. Copies of the certified copies of the pri application from the International B	Bureau (PCT Rule 17.2(a)).	•			
* See the attached detailed Office action for a lis					
14) ☐ Acknowledgment is made of a claim for domes					
 a)					
Attachment(s)					
Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawing Review (PTO-948) Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449) Paper No(s)	5) Notice of I	Summary (PTO-413) Paper No(s) Informal Patent Application (PTO-152)			
Patent and Trademark Office TO-326 (Rev. 04-01) Office I	Action Summary	Part of Paper No. 20			

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DETAILED ACTION

This action is in response to (1) the IDS filed 25 July 2002, (2) Amendment B, filed 29 August 2002, Paper No. 16, and (3) the RCE filed 4 October 2002, Paper No. 19.

Continued Examination Under 37 CFR 1.114

1. A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on 29 August 2002 has been entered.

Double Patenting

2. Applicant is advised that should claim 7 be found allowable, claim 5 will be objected to under 37 CFR 1.75 as being a substantial duplicate thereof. When two claims in an application are duplicates or else are so close in content that they both cover the same thing, despite a slight difference in wording, it is proper after allowing one claim to object to the other as being a substantial duplicate of the allowed claim. See MPEP § 706.03(k).

Claim Rejections - 35 USC § 103

- 3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person

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having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

4. Claims 1-6 and 7-10 are rejected under 35 U.S.C. 103(a) as being unpatentable over the article Im et al. "Single-crystal Si films for thin-film transistor devices" <u>Applied Physics Letters</u> 70(25) 23 June 1997, pp. 3434-3436 (the article provided by Applicant) in view of US 5,492,843 (Adachi et al.)

Regarding claims 1, 5, and 7, Im discloses a method for forming a crystalline semiconductor film at a desired position on a substrate comprising,

preparing a substrate having deposited thereon, amorphous (i.e. first property) semiconductor silicon (a-Si);

preparing an optical mask having a pattern thereon and spacing the mask apart from the substrate;

positioning the mask at the desired position;

irradiating the a-Si through the mask pattern to convert the desired exposed regions to polycrystalline and single crystalline (i.e. second property) semiconductor silicon (Figs. 1 and 2 and captions thereunder);

wherein the crystallized silicon film is for the production of thin film transistors TFTs.

(See whole article -- especially the Abstract, paragraph bridging the cols. on p. 3434 and p. 3436, left-hand col., last paragraph.)

Im does not indicate that an insulation film is formed on both the crystalline silicon and a-Si. Regarding claim 8, Im also does not indicate that the silicon film is patterned to form crystalline silicon islands. However, Im does indicate that the crystallized silicon film --

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especially the single crystal region—is used to form a TFT which suggests to one of ordinary skill that additional processing to form the TFT will be necessary.

Adachi teaches a method of forming a TFT (Fig. 1A-1E) by blanket depositing a silicon film 53 (Fig. 5A) and then forming an insulation film 54 over the silicon to protect it from contamination during patterning (Fig. 5B) to form Si islands (Fig. 5C) from which the TFT active region is formed (col. 7, lines 26-58).

It would have been obvious for one of ordinary skill in the art, at the time of the invention to blanket deposit the insulation film of **Adachi** over both the a-Si and crystallized silicon of **Im** in order to protect the crystallized silicon film region of **Im** from contamination during the patterning to form crystalline silicon islands on which the TFT active regions are formed. The patterning to form islands is standard in the art for TFT fabrication as shown in **Adachi** and is an obvious modification to **Im** because **Im** teaches that the single crystal silicon region is the best for forming a TFT.

Regarding claims 2 and 9, **Im** shows in Fig. 1 that an alignment mark exists on the substrate, wherein the alignment mark is used to position the projected area of the optical mask. Note that the first chevron serves as the alignment mark for the other chevrons as shown in Fig. 1.

Regarding claims 3, 6, and 10, the mask used in **Im** necessarily has the alignment pattern mark, otherwise the alignment mark could not be made in the a-Si film by laser crystallization. As shown in Fig. 1, the alignment mark is visible based upon the differences in the optical characteristics of amorphous, polycrystalline, and single crystal silicon.

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Regarding claim 4, the Im Fig. 1 shows the plural positionings of the laser relative to the

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substrate is performed based upon the alignment mark because there is shown a regular,

repetitive patterns of chevrons.

Response to Arguments

5. Applicant's arguments with respect to claims 1-10 have been considered but are moot in

view of the new ground(s) of rejection.

Conclusion

Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Erik Kielin whose telephone number is 703-306-5980. The

examiner can normally be reached on 9:00 - 19:30 on Monday through Thursday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Carl Whitehead, Jr., can be reached at 703-308-4940. The fax phone numbers for the

organization where this application or proceeding is assigned are 703-872-9318 for regular

communications and 703-872-9319 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding

should be directed to the receptionist whose telephone number is 703-308-0956.

Erik Kielin

Erikuli

November 7, 2002